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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	1	of	1

Complete If Known	
Application Number	10/077,784
Filing Date	February 20, 2002
First Named Inventor	Terry L. Gilton
Art Unit	2818
Examiner Name	~~Not Yet Assigned~~ PHAN
Attorney Docket Number	M4065.0482/P482

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number-Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
TP	A	5,883,827	3/16/1999	Morgan	

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Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3]-Number[4]-Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

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Examiner Signature	Trong Phan	Date Considered	1/22/04

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	AL				
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Group Art Unit	2818
Examiner Name	~~Not Yet Assigned~~ PHAN
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Examiner Signature	Trong Phan	Date Considered	1/22/04

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Sheet	1	of	4

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Application Number	10/077,784
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First Named Inventor	Gilton, et al.
Art Unit	2818
Examiner Name	T. Phan
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Examiner Signature	Trong Phan	Date Considered	1/22/04

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete If Known	
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Filing Date	February 20, 2002
First Named Inventor	Terry L. Gilton
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Attorney Docket Number	M4065.0482/P482

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
TP	AA	6,469,364-B1	10-22-2002	Kozicki	
TP	AB	2002/0168820-A1	11-14-2002	Kozicki et al.	

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Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3]-Number[4]-Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

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